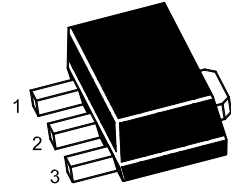


2N2222AU

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

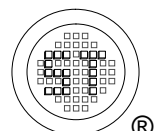
Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	75	V
Collector Emitter Voltage	V_{CEO}	40	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	600	mA
Power Dissipation ¹⁾	P_{tot}	625	mW
Power Dissipation ²⁾	P_{tot}	1.1	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	200 ¹⁾ 114 ²⁾	$^\circ\text{C/W}$

¹⁾ Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.

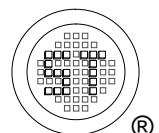
²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.



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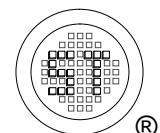
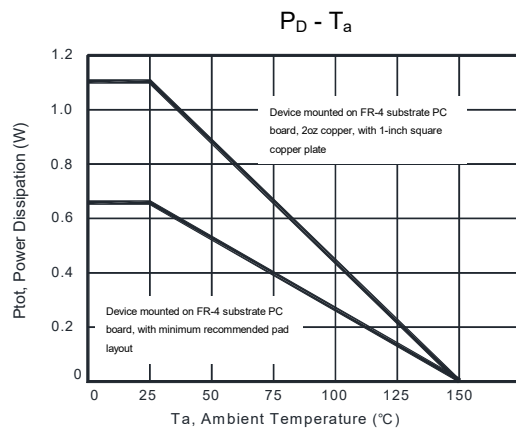
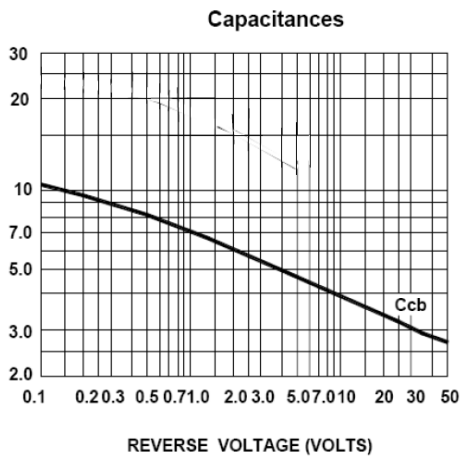
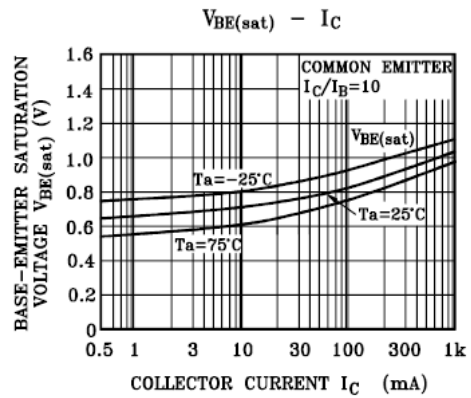
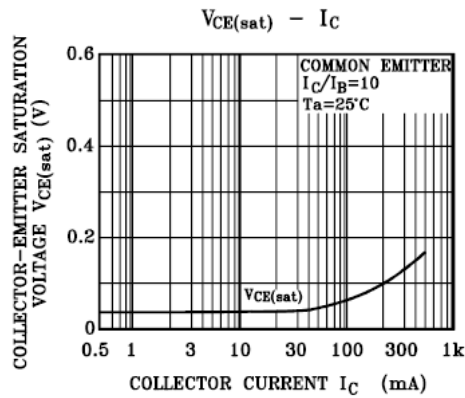
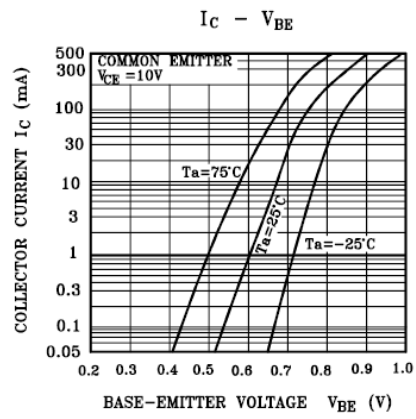
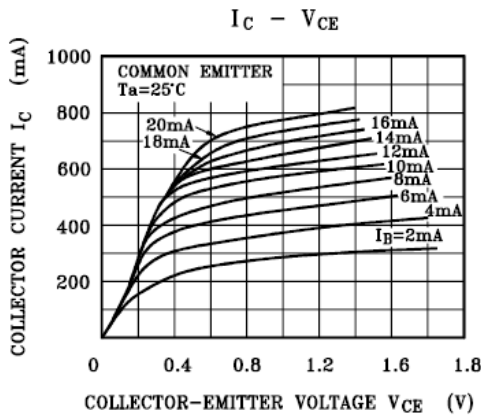
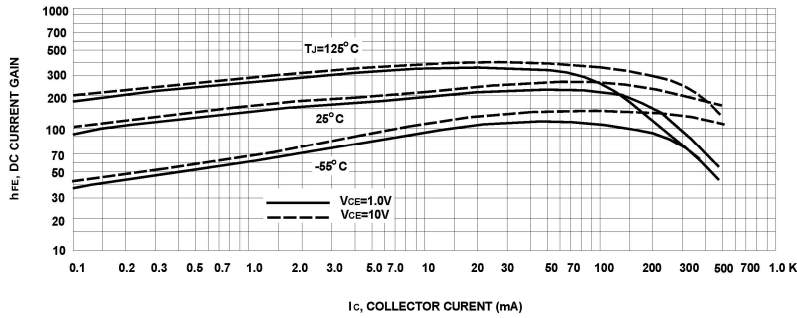
Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 10\text{ V}$, $I_C = 0.1\text{ mA}$ at $V_{CE} = 10\text{ V}$, $I_C = 1\text{ mA}$ at $V_{CE} = 10\text{ V}$, $I_C = 10\text{ mA}$ at $V_{CE} = 10\text{ V}$, $I_C = 150\text{ mA}$ at $V_{CE} = 10\text{ V}$, $I_C = 500\text{ mA}$	h_{FE} h_{FE} h_{FE} h_{FE} h_{FE}	35 50 75 100 40	- - - 300 -	- - - - -
Collector Base Cutoff Current at $V_{CB} = 60\text{ V}$	I_{CBO}	-	10	nA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	75	-	V
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	40	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$ at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{CE(sat)}$	- -	0.3 1	V
Base Emitter Saturation Voltage at $I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$ at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{BE(sat)}$	0.6 -	1.2 2	V
Gain Bandwidth Product at $I_C = 20\text{ mA}$, $V_{CE} = 20\text{ V}$, $f = 100\text{ MHz}$	f_T	250	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	8	pF



Electrical Characteristics Curves

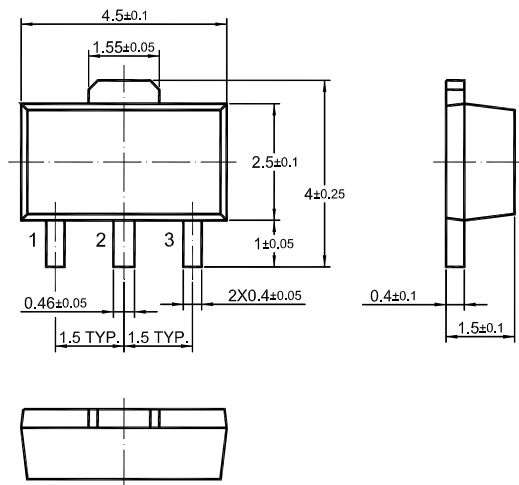
Figure 1. DC Current Gain



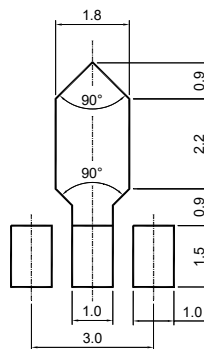
2N2222AU

Package Outline (Dimensions in mm)

SOT-89



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-89	12	8 ± 0.1	0.315 ± 0.004	178	7	1,000
				330	13	4,000

Marking information

" 2N2222AU " = Part No.
 "YM" = Date Code Marking
 "Y" = Year
 "M" = Month
 Font type: Arial

